

isc Silicon NPN Power Transistor

BU603

DESCRIPTION

- Collector-Emitter Sustaining Voltage-
: $V_{CEO(SUS)} = 550V$ (Min)
- High Switching Speed

APPLICATIONS

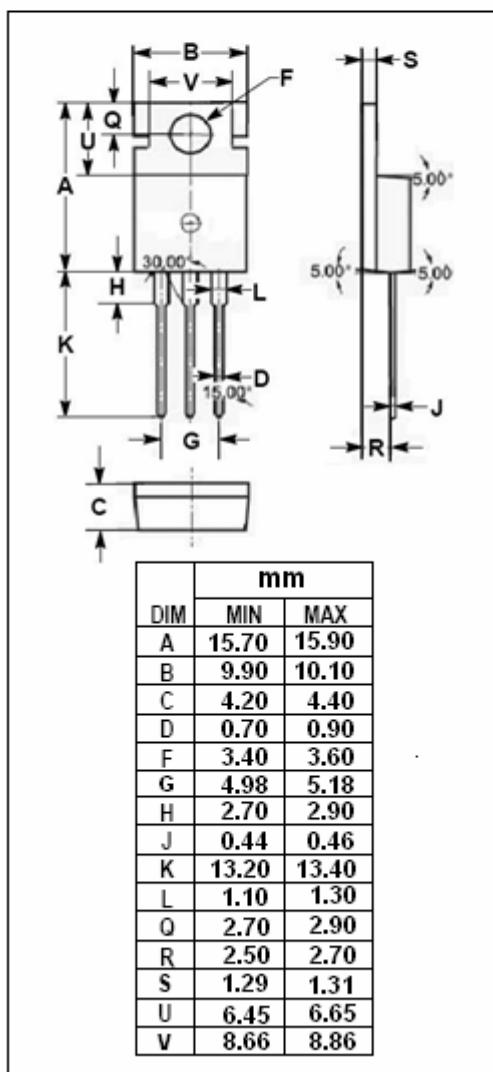
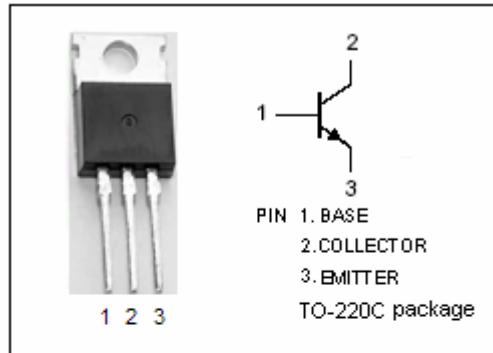
- Designed for use in power supplies and deflection circuits for color receivers and monitors

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CES}	Collector-Emitter Voltage- $V_{BE}= 0$	1350	V
V_{CEO}	Collector-Emitter Voltage	550	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	5	A
I_{CM}	Collector Current-Peak	8	A
I_B	Base Current-Continuous	2	A
I_{BM}	Base Current-Peak	4	A
I_E	Emitter Current-Continuous	7	A
I_{EM}	Emitter Current-Peak	12	A
P_c	Collector Power Dissipation $T_c=25^\circ C$	100	W
T_j	Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-65~150	$^\circ C$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance,Junction to Case	1.25	$^\circ C/W$



isc Silicon NPN Power Transistor**BU603****ELECTRICAL CHARACTERISTICS****T_c=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-Emitter Sustaining Voltage	I _C = 100mA; I _B = 0	550			V
V _{CE(sat)-1}	Collector-Emitter Saturation Voltage	I _C = 2A; I _B = 0.33A			2	V
V _{CE(sat)-2}	Collector-Emitter Saturation Voltage	I _C = 4A; I _B = 1.33A			3	V
I _{CES}	Collector Cutoff Current	V _{CE} = V _{CESmax} ; V _{BE} = 0 V _{CE} = V _{CESmax} ; V _{BE} = 0; T _J = 125°C			1 2	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 6V; I _C = 0			1	mA
h _{FE-1}	DC Current Gain	I _C = 10mA ; V _{CE} = 5V	6			
h _{FE-2}	DC Current Gain	I _C = 1A ; V _{CE} = 5V	8			
h _{FE-3}	DC Current Gain	I _C = 2A ; V _{CE} = 2V	6			
h _{FE-4}	DC Current Gain	I _C = 4A ; V _{CE} = 3V	3			

Switching Times; Resistive Load

t _{on}	Turn-On Time	I _C = 2A; I _{B1} = -I _{B2} = 0.33A			0.5	μ s
t _s	Storage Time				6.0	μ s
t _f	Fall Time				0.7	μ s